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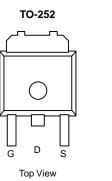
## P-Channel 30 V (D-S) MOSFET

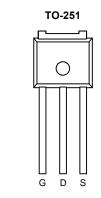
PRODUCT SUMMARY				
V <sub>DS</sub> (V)	R <sub>DS(on)</sub> (Ω)	I <sub>D</sub> (A) <sup>a</sup>		
- 30	0.0073 at V <sub>GS</sub> = - 10 V	-85		
- 30	0.009 at $V_{GS}$ = - 4.5 V	-80		

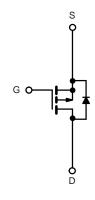
#### **FEATURES**

Compliant to RoHS Directive 2002/95/EC









P-Channel MOSFET

<b>ABSOLUTE MAXIMUM RAT</b>	INGS (T <sub>C</sub> = 25 °C, unless other	rwise noted)		
Parameter	Symbol	Limit	Unit	
Gate-Source Voltage		V <sub>GS</sub>	± 20	V
Continuous Drain Current (T <sub>1</sub> = 175 °C)	T <sub>C</sub> = 25 °C	1	- 85 <sup>a</sup>	А
Continuous Drain Current $(I_J = 175^{\circ}C)$	T <sub>C</sub> = 125 °C	I <sub>D</sub>	- 68	
Pulsed Drain Current	I <sub>DM</sub>	- 260	A	
Avalanche Current	I <sub>AR</sub>	- 67		
Repetitive Avalanche Energy <sup>b</sup>	L = 0.1 mH	E <sub>AR</sub>	186	mJ
Power Dissipation	T <sub>C</sub> = 25 °C (TO-220AB and TO-263)	Р	187 <sup>d</sup>	W
Power Dissipation	T <sub>A</sub> = 25 °C (TO-263) <sup>c</sup>	PD	3.75	vv
Operating Junction and Storage Temperature Range		T <sub>J</sub> , T <sub>stg</sub>	- 55 to 175	°C

THERMAL RESISTANCE RATINGS				
Parameter		Symbol	Limit	Unit
Junction-to-Ambient	PCB Mount (TO-251) <sup>c</sup>	P	40	
Junction-to-Ambient	Free Air (TO-252)	– R <sub>thJA</sub>	62.5	°C/W
Junction-to-Case		R <sub>thJC</sub>	0.8	

Notes:

a. Package limited.

b. Duty cycle  $\leq$  1 %.

c. When mounted on 1" square PCB (FR-4 material).

d. See SOA curve for voltage derating.

\* Pb containing terminations are not RoHS compliant, exemptions may apply.

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<b>SPECIFICATIONS</b> ( $T_J = 25$ Parameter	Symbol	Test Conditions	Min.	Тур.	Max.	Unit	
Static	Symbol	Test conditions	WIII.	Typ.		Unit	
Drain-Source Breakdown Voltage	V <sub>DS</sub>	V <sub>GS</sub> = 0 V, I <sub>D</sub> = - 250 µA	- 30				
Gate Threshold Voltage		$V_{\rm DS} = V_{\rm GS}, I_{\rm D} = -250 \mu\text{A}$	- 30		- 3	V	
•	V <sub>GS(th)</sub>	$V_{DS} = V_{GS}, I_D = -250 \mu \text{A}$ $V_{DS} = 0 \text{V},  V_{GS} = \pm 20 \text{V}$	- 1		± 100	nA	
Gate-Body Leakage	I <sub>GSS</sub>					ΠA	
Zero Coto Valtago Droin Current		$V_{DS} = -30 \text{ V}, V_{GS} = 0 \text{ V}$			- 1	μΑ	
Zero Gate Voltage Drain Current	IDSS	$V_{DS} = -30 \text{ V}, V_{GS} = 0 \text{ V}, T_{J} = 125 \text{ °C}$			- 50		
		$V_{DS} = -30 \text{ V}, V_{GS} = 0 \text{ V}, T_{J} = 175 \text{ °C}$			- 250		
On-State Drain Current <sup>a</sup>	I <sub>D(on)</sub>	V <sub>DS</sub> = - 5 V, V <sub>GS</sub> = - 10 V	- 120			A	
		V <sub>GS</sub> = - 10 V, I <sub>D</sub> = - 30 A		0.0073	0.0082		
Drain-Source On-State Resistance <sup>a</sup>	R <sub>DS(on)</sub>	$V_{GS}$ = - 10 V, I <sub>D</sub> = - 30 A, T <sub>J</sub> = 125 °C			0.0115	Ω	
	D3(01)	$V_{GS}$ = - 10 V, I <sub>D</sub> = - 30 A, T <sub>J</sub> = 175 °C			0.0131		
		V <sub>GS</sub> = - 4.5 V, I <sub>D</sub> = - 20 A		0.009	0.010	)	
Forward Transconductance <sup>a</sup>	9 <sub>fs</sub>	V <sub>DS</sub> = - 15 V, I <sub>D</sub> = - 75 A	20			S	
Dynamic <sup>b</sup>							
Input Capacitance	C <sub>iss</sub>			1089			
Output Capacitance	C <sub>oss</sub>	$V_{GS}$ = 0 V, $V_{DS}$ = - 25 V, f = 1 MHz		759		pF	
Reversen Transfer Capacitance	C <sub>rss</sub>			419			
Total Gate Charge <sup>c</sup>	Qg			130	280	nC	
Gate-Source Charge <sup>c</sup>	Q <sub>gs</sub>	$V_{DS}$ = - 15 V, $V_{GS}$ = - 10 V, $I_{D}$ = - 75 A		62			
Gate-Drain Charge <sup>c</sup>	Q <sub>gd</sub>			39			
Turn-On Delay Time <sup>c</sup>	t <sub>d(on)</sub>			25	30		
Rise Time <sup>c</sup>	tr	V <sub>DD</sub> = - 15 V, R <sub>I</sub> = 0.2 Ω		225	300	ns	
Turn-Off Delay Time <sup>c</sup>	t <sub>d(off)</sub>	$I_D \cong$ - 75 Å, $V_{GEN}$ = - 10 V, $R_g$ = 2.5 $\Omega$		150	210		
Fall Time <sup>c</sup>	t <sub>f</sub>			210	290		
Source-Drain Diode Ratings and Cha	racteristics <sup>b</sup>	(T <sub>C</sub> = 25 °C)			I		
Continuous Current	۱ <sub>S</sub>				- 85	А	
Pulsed Current	I <sub>SM</sub>				- 260		
Forward Voltage <sup>a</sup>	V <sub>SD</sub>	I <sub>F</sub> = - 75 A, V <sub>GS</sub> = 0 V		- 1.2	- 1.5	V	
Reverse Recovery Time	t <sub>rr</sub>			55	100	ns	
Peak Reverse Recovery Current	I <sub>RM(REC)</sub>	I <sub>F</sub> = - 75 A, dI/dt = 100 A/μs		2.5	5	А	
Reverse Recovery Charge	Q <sub>rr</sub>			0.07	0.25	uС	

Notes:

a. Pulse test; pulse width  $\leq$  300 µs, duty cycle  $\leq$  2 %.

b. Guaranteed by design, not subject to production testing.

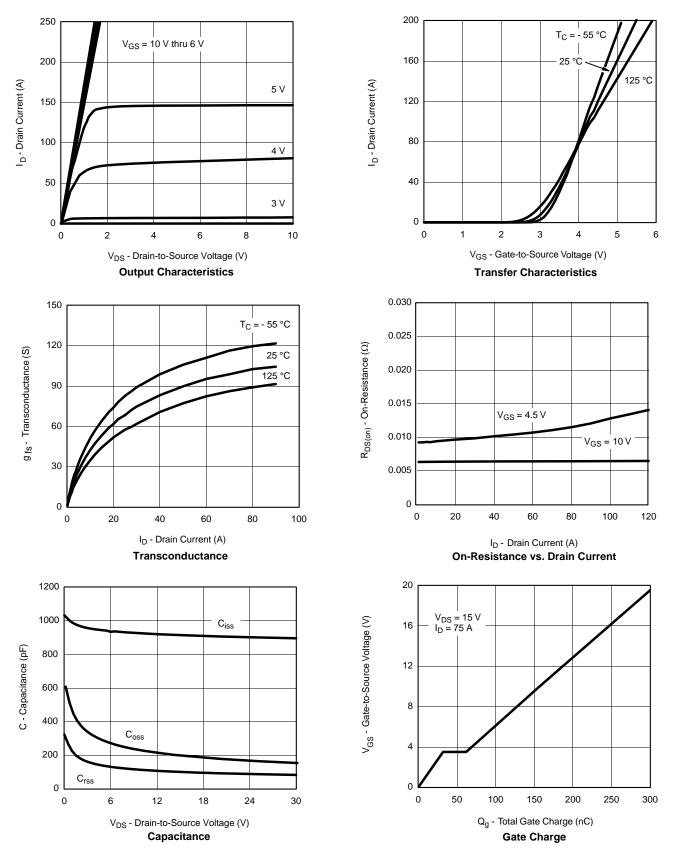
c. Independent of operating temperature.

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.



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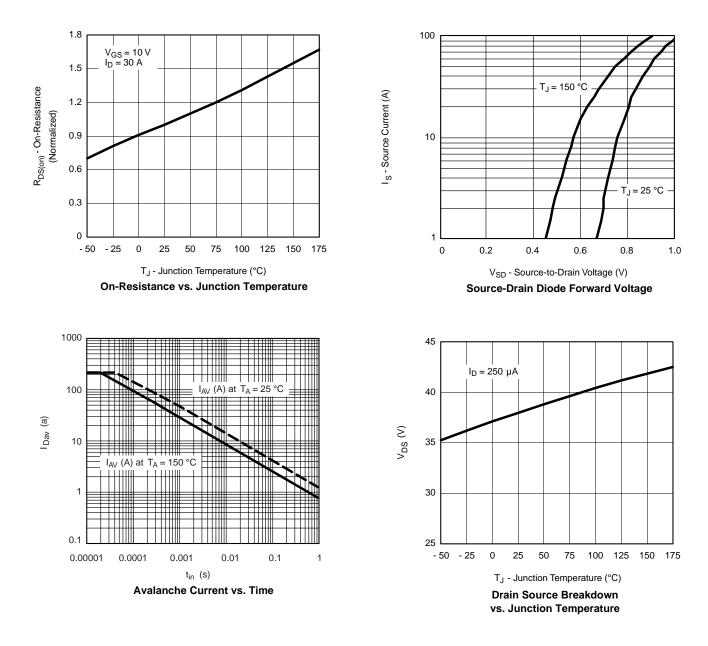






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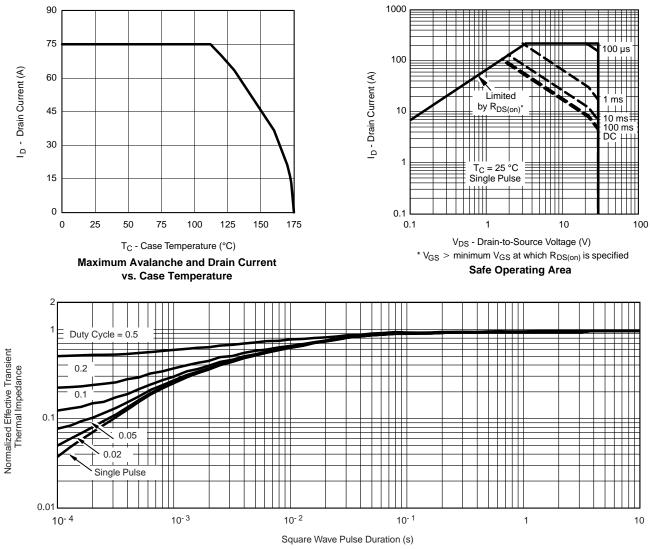
#### TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)





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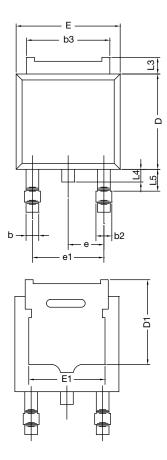
#### **THERMAL RATINGS**



Normalized Thermal Transient Impedance, Junction-to-Case









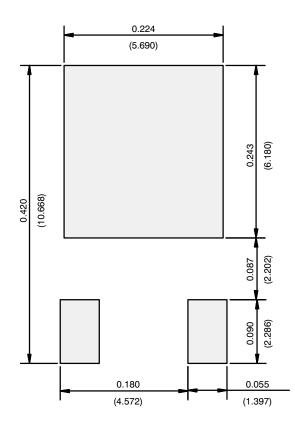
	MILLIN	IETERS	INC	HES	
DIM.	MIN.	MAX.	MIN.	MAX.	
А	2.18	2.38	0.086	0.094	
A1	-	0.127	-	0.005	
b	0.64	0.88	0.025	0.035	
b2	0.76	1.14	0.030	0.045	
b3	4.95	5.46	0.195	0.215	
С	0.46	0.61	0.018	0.024	
C2	0.46	0.89	0.018	0.035	
D	5.97	6.22	0.235	0.245	
D1	5.21	-	0.205	-	
Е	6.35	6.73	0.250	0.265	
E1	4.32	-	0.170	-	
Н	9.40	10.41	0.370	0.410	
е	2.28 BSC 0.090 BSC				
e1	4.56	BSC	0.180 BSC		
L	1.40	1.78	0.055	0.070	
L3	0.89	1.27	0.035	0.050	
L4	-	1.02	-	0.040	
L5	1.14	1.52	0.045	0.060	
ECN: X12- DWG: 5347	0247-Rev. M, 7	24-Dec-12			

#### Note

• Dimension L3 is for reference only.



#### **RECOMMENDED MINIMUM PADS FOR DPAK (TO-252)**

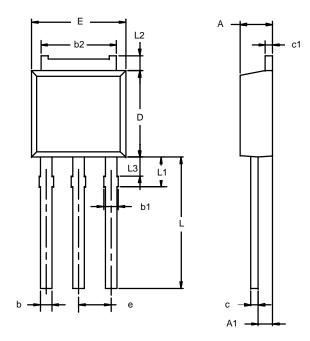


Recommended Minimum Pads Dimensions in Inches/(mm)



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### TO-251AA (DPAK)



Note: Dimension L3 is for reference only.

	MILLIN	IETERS	INCHES		
Dim	Min	Мах	Min	Max	
Α	2.21	2.38	0.087	0.094	
A1	0.89	1.14	0.035	0.045	
b	0.71	0.89	0.028	0.035	
b1	0.76	1.14	0.030	0.045	
b2	5.23	5.43	0.206	0.214	
С	0.46	0.58	0.018	0.023	
c1	0.46	0.58	0.018	0.023	
D	5.97	6.22	0.235	0.245	
Е	6.48	6.73	0.255	0.265	
е	2.28 BSC		0.090 BSC		
L	8.89	9.53	0.350	0.375	
L1	1.91	2.28	0.075	0.090	
L2	0.89	1.27	0.035	0.050	
L3	1.15	1.52	0.045	0.060	

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